2CL2FE

200mA 6.0kV 100nS--High Voltage Silicon Rectifier Diode

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. High frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

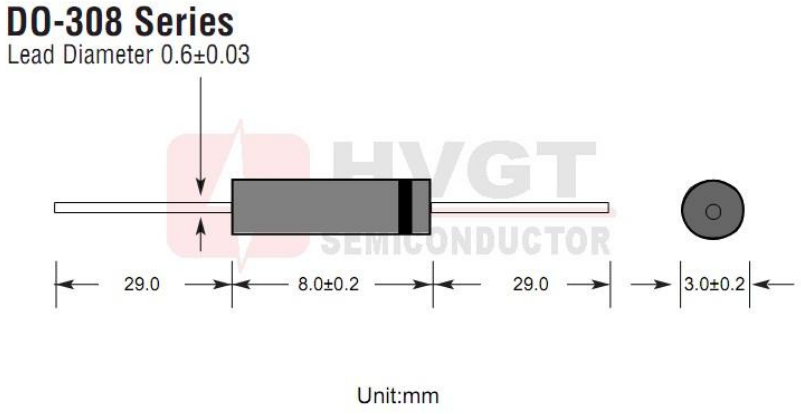
1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. Other.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.28 grams (approx).

SHAPE DISPLAY:

SIZE: (Unit:mm) **HVGT NAME: DO-308**



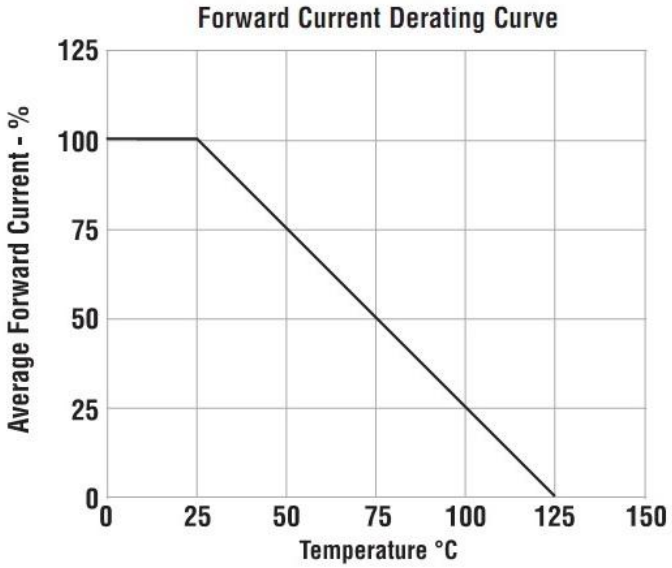
MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

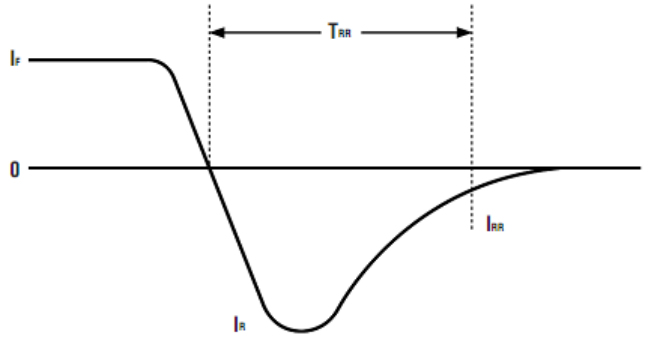
Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	V_{RRM}	T_A=25°C	6.0	kV
Average Forward Current Maximum	I_{FAVM}	T_A=25°C	200	mA
		T_{OIL}=--°C	--	mA
Suege Current	I_{FSM}	T_A=25°C; Half-Sine Wave; 8.3mS	10	A
Junction Temperature	T_J		-40~+125	°C
Allowable Operation Case Temperature	Tc		125	°C
Storage Temperature	T_{STG}		-40~+125	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at 25°C; at $I_{F(AV)}$	18	V
Maximum Reverse Current	I_R1	at 25°C; at V_{RRM}	2.0	uA
	I_R2	at 100°C; at V_{RRM}	20	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	100	nS
Junction Capacitance	C_J	at 25°C; V_R=0V; f=1MHz	15	pF

Fig 1	Fig 2
Forward Current Derating Curve	Reverse Recovery Measurement Waveform

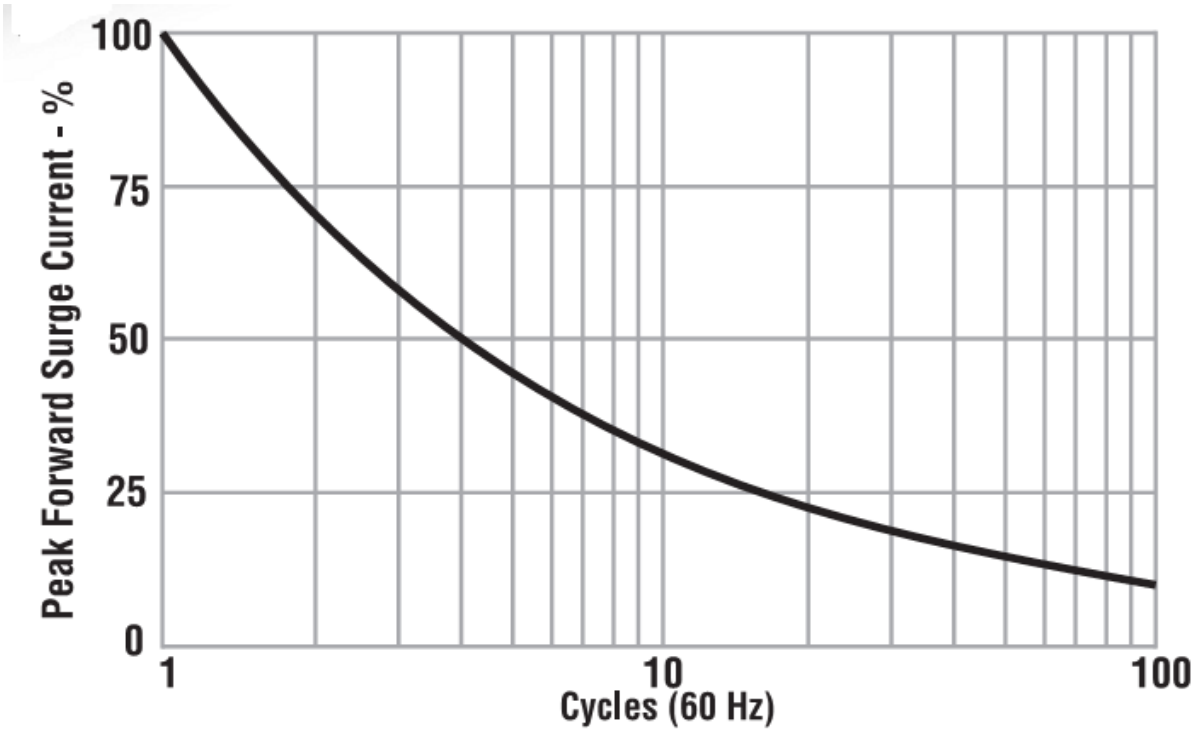




Typical data capture points: I_F =0.5I_R , I_R,I_{RR} =0.25I_R

Fig 3

Non-Repetitive Surge Current



Marking	Type	Code	Cathode Mark
	2CL2FE	--	